



EconoPACK™ mit schnellem Trench/Feldstop IGBT³ und Emitter Controlled³ Diode
EconoPACK™ with fast trench/fieldstop IGBT³ and Emitter Controlled³ diode

**Vorläufige Daten
Preliminary Data**

IGBT, Wechselrichter / IGBT, Inverter

Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	600	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 70^{\circ}\text{C}, T_{vj\text{ max}} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$	75	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	150	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{ max}} = 175$	P_{tot}	250	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,45 1,60 1,70	1,90	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 1,20\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	4,9	5,8	6,5	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,80			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0			Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	4,60			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,145			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,025 0,025 0,025			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,02 0,02 0,02			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,21 0,24 0,25			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,06 0,07 0,07			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 4000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	0,35 0,50 0,60			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 75\text{ A}, V_{CE} = 300\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 5,1\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	2,40 2,80 3,00			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 360\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	530 380			A A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}			0,60	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}			0,20	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

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**Vorläufige Daten
Preliminary Data**

**Diode, Wechselrichter / Diode, Inverter
Höchstzulässige Werte / Maximum Rated Values**

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	600	V
Dauergleichstrom Continuous DC forward current		I_F	75	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	150	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	660	A^2s
	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$		610	A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 75\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,55	1,95	V
	$I_F = 75\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		1,50		V
	$I_F = 75\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,45		V
Rückstromspitze Peak reverse recovery current	$I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		100		A
		$T_{vj} = 125^{\circ}\text{C}$		115		A
		$T_{vj} = 150^{\circ}\text{C}$		125		A
Sperrverzögerungsladung Recovered charge	$I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		3,00		μC
		$T_{vj} = 125^{\circ}\text{C}$		6,00		μC
		$T_{vj} = 150^{\circ}\text{C}$		7,50		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 75\text{ A}, -di_F/dt = 4000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		0,95		mJ
		$T_{vj} = 125^{\circ}\text{C}$		1,50		mJ
		$T_{vj} = 150^{\circ}\text{C}$		1,85		mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode	R_{thJC}			0,95	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		0,30		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5,00		$\text{k}\Omega$
Abweichung von R100 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung Power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		t.b.d.		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		t.b.d.		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

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**Vorläufige Daten
Preliminary Data**

Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolation (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		7,5		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 225		
			min.	typ.	max.
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	0,02		K/W
Modulstreuintduktivität Stray inductance module		L _{sCE}	19		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _c = 25°C, pro Schalter / per switch	R _{CC+EE'}	2,50		mΩ
Lagertemperatur Storage temperature		T _{stg}	-40	125	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
Gewicht Weight		G	180		g

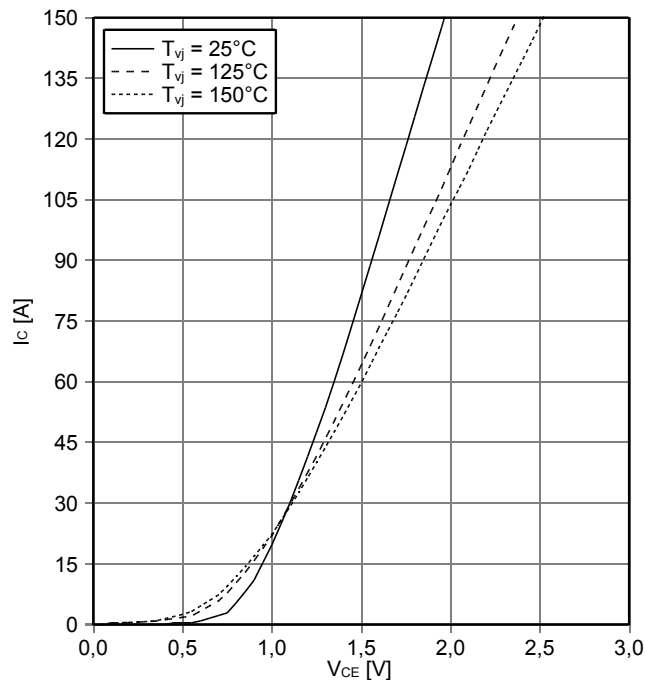
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Vorläufige Daten
Preliminary Data

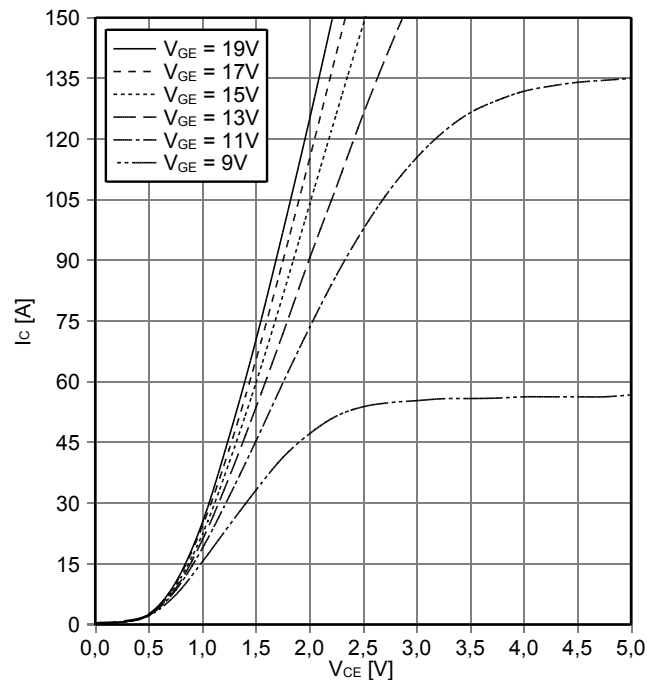
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



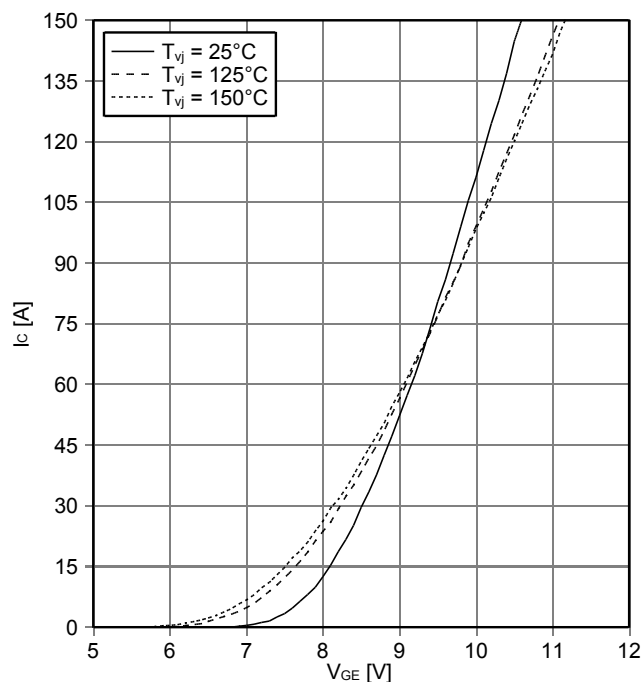
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



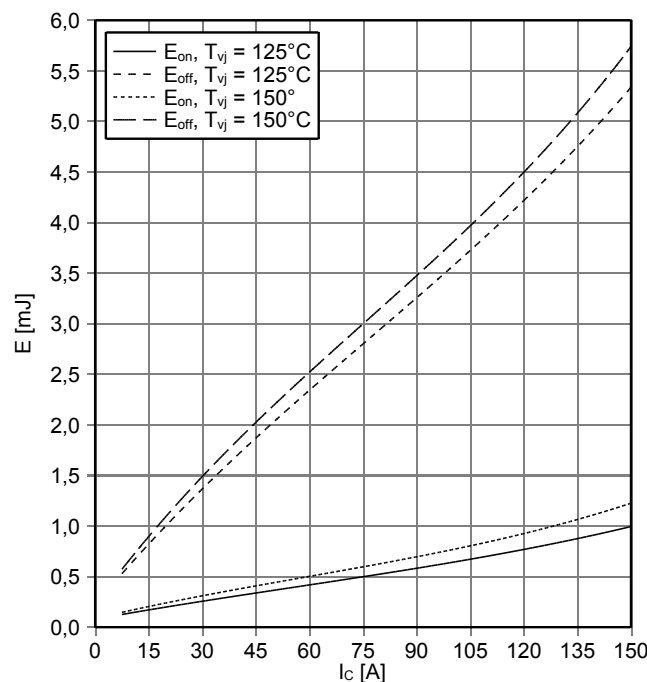
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 5.1\ \Omega$, $R_{Goff} = 5.1\ \Omega$, $V_{CE} = 300\text{ V}$



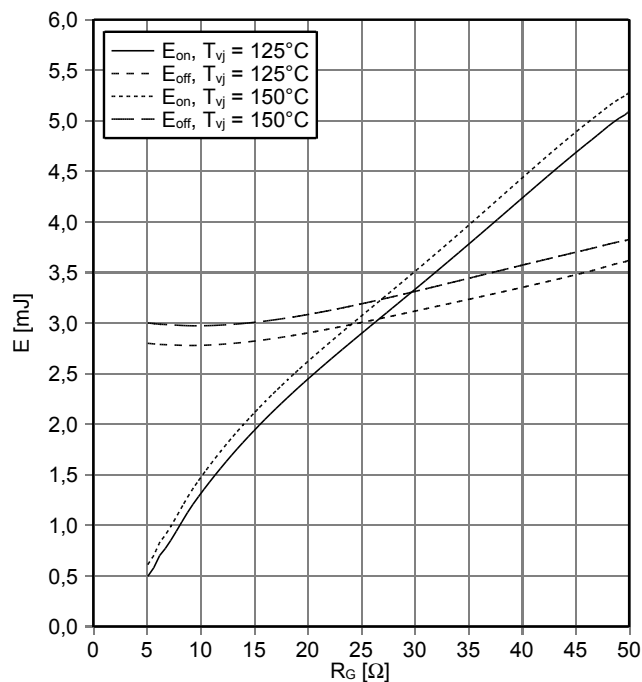
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**Vorläufige Daten
Preliminary Data**

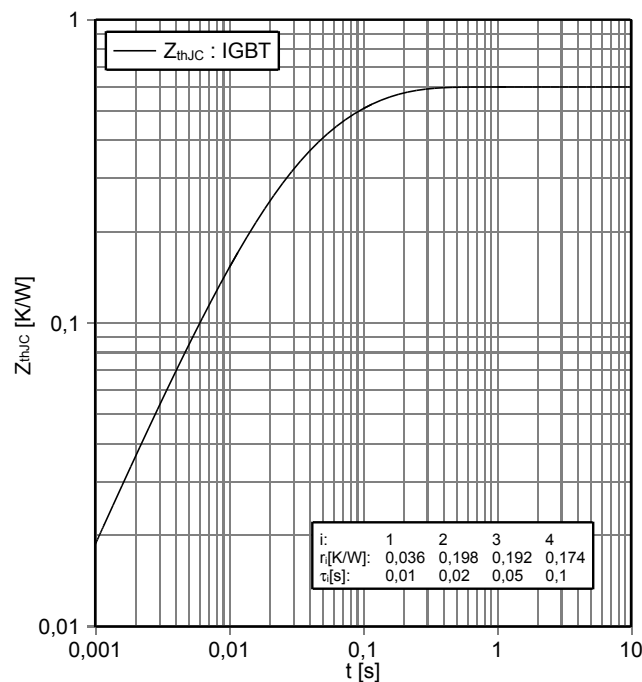
**Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)**

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 V, I_C = 75 A, V_{CE} = 300 V$



**Transienter Wärmewiderstand IGBT, Wechselrichter
transient thermal impedance IGBT, Inverter**

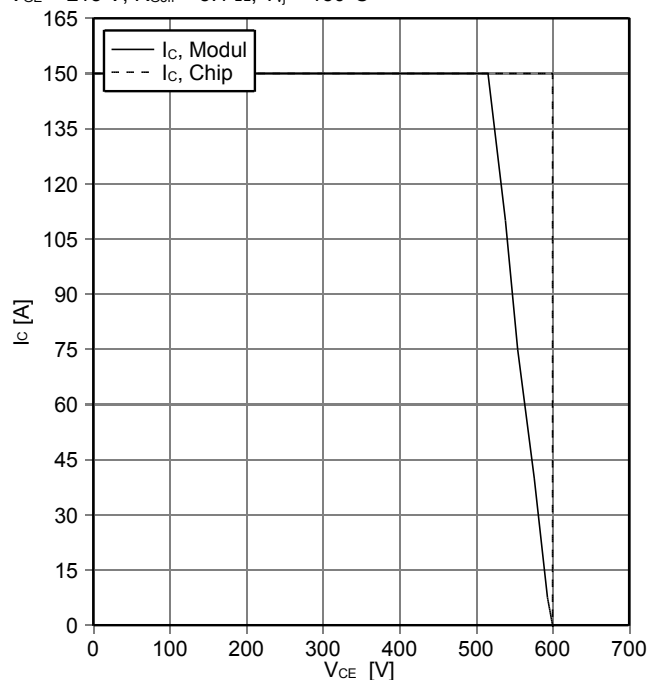
$Z_{thJC} = f(t)$



**Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter
(RBSOA)**

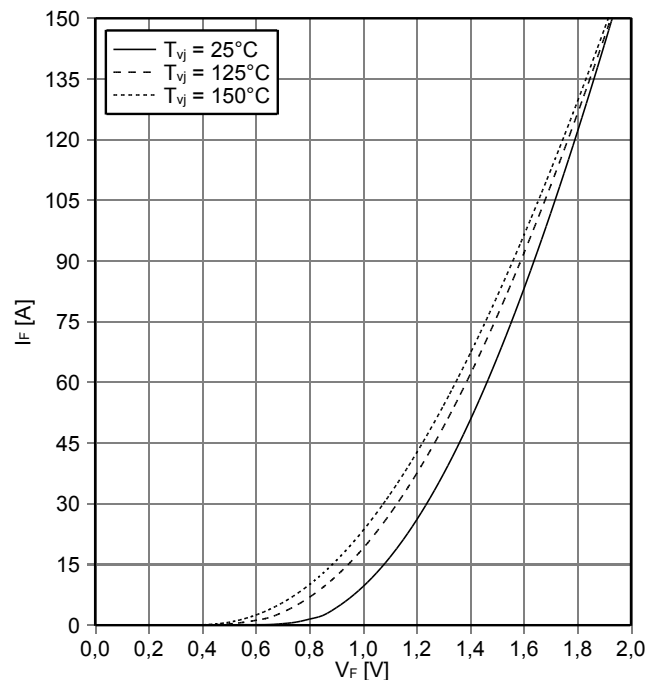
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 V, R_{Goff} = 5.1 \Omega, T_{vj} = 150^\circ C$



**Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)**

$I_F = f(V_F)$

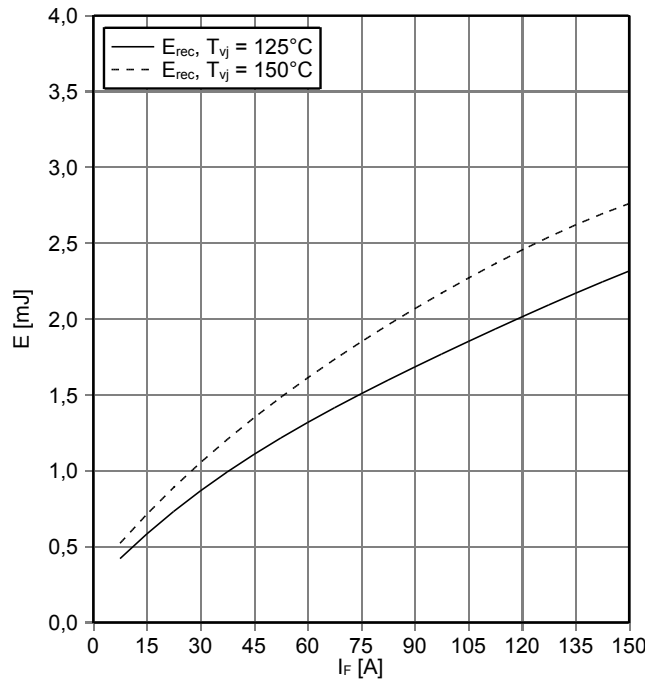


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Vorläufige Daten
Preliminary Data

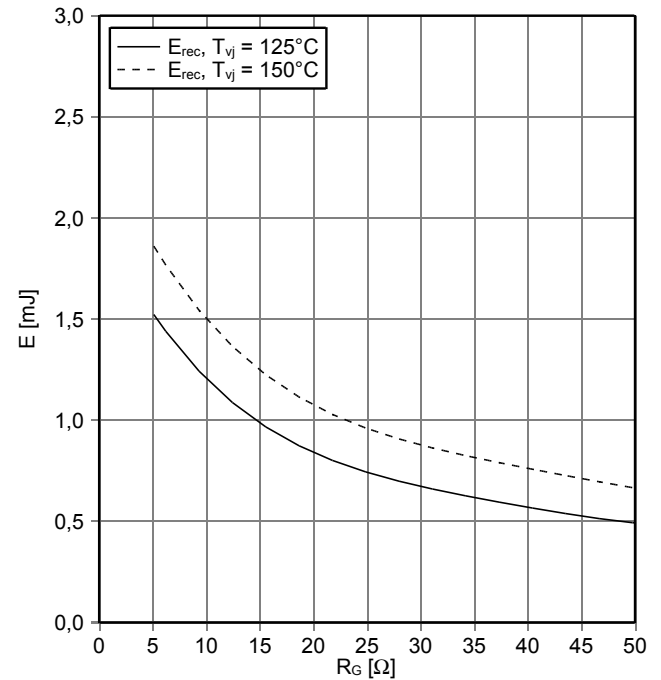
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 5.1 \Omega, V_{CE} = 300 V$



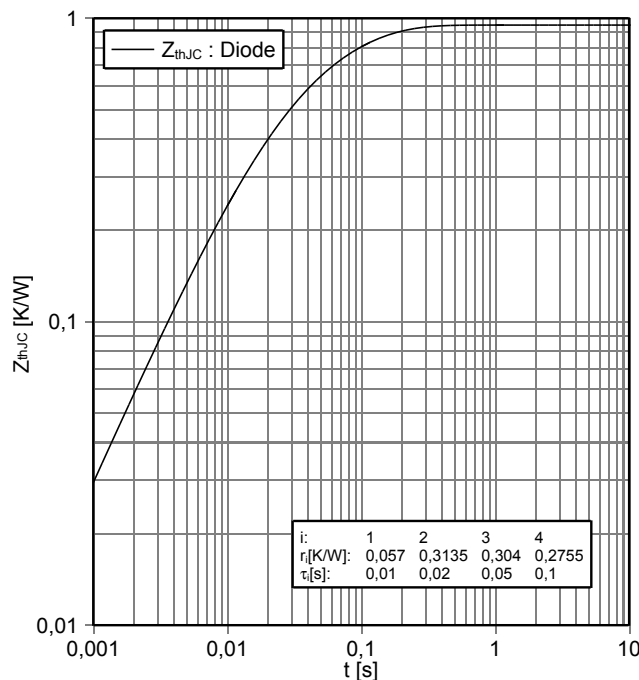
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 75 A, V_{CE} = 300 V$



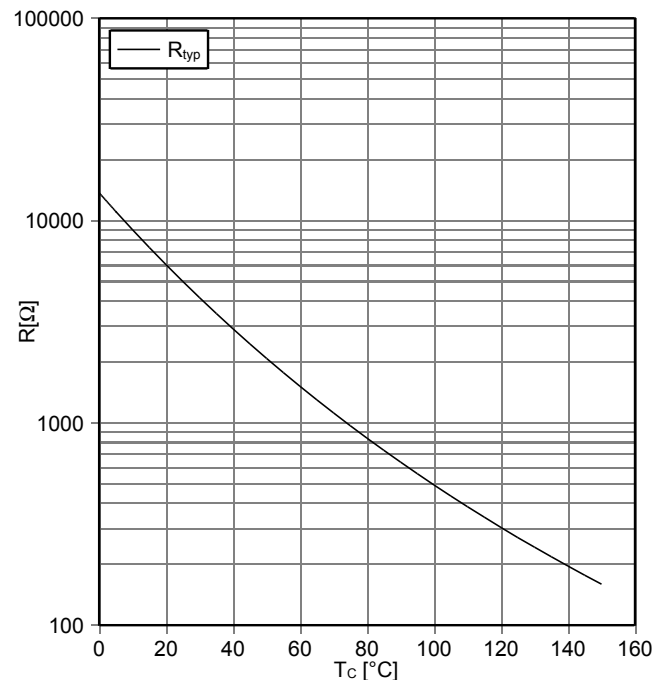
Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)

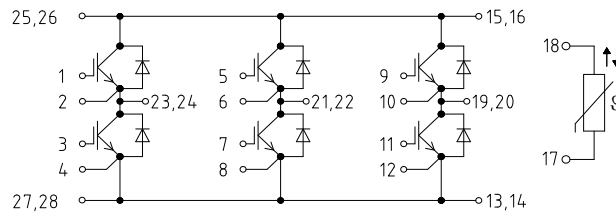
$R = f(T)$



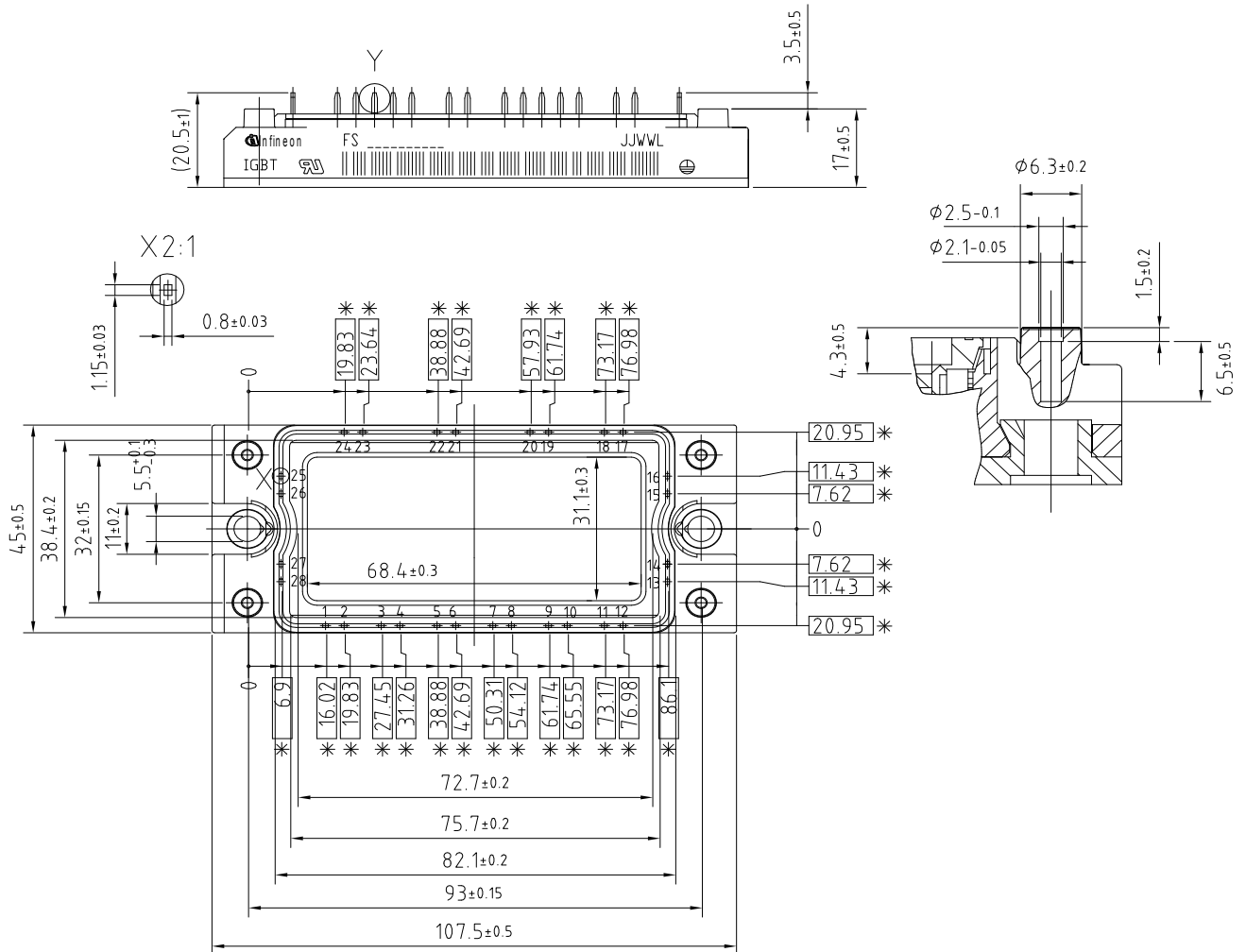
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Vorläufige Daten
Preliminary Data

Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



* = alle Maße mit einer Toleranz von ± 0.4
 * = all dimensions with tolerance of ± 0.4

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